

N-Channel Super Trench Power MOSFET

Description

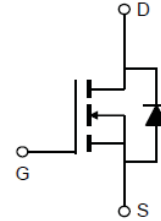
The RM110N150HD uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

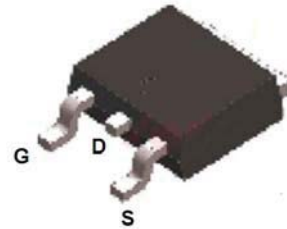
- $V_{DS} = 150V, I_D = 110A$
 $R_{DS(ON)} < 7.8m\Omega @ V_{GS} = 10V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



Schematic diagram



TO-263-2L top view

100% UIS TESTED!

100% ΔV_{ds} TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
110N150	RM110N150HD	TO-263-2L	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	110	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	93	A
Pulsed Drain Current	I_{DM}	440	A
Maximum Power Dissipation	P_D	300	W
Derating factor		2	W/ $^\circ C$
Single pulse avalanche energy ^(Note 5)	E_{AS}	1296	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	0.5	$^\circ C/W$
--	-----------------	-----	--------------

Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

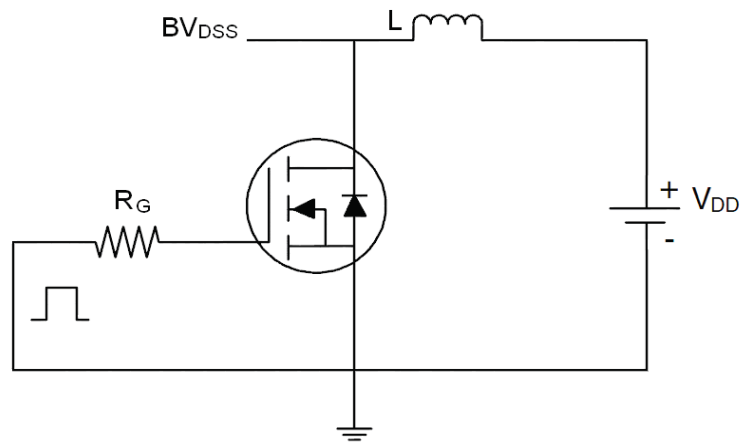
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	150	147	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=150V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.5	-	4.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=55A$	-	6	7.8	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=10V, I_D=55A$	70	-	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{ISS}	$V_{DS}=75V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	10000	-	PF
Output Capacitance	C_{OSS}		-	2046	-	PF
Reverse Transfer Capacitance	C_{RSS}		-	55	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=75V, I_D=55A$ $V_{GS}=10V, R_G=4.7\Omega$	-	30	-	nS
Turn-on Rise Time	t_r		-	52	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	69	-	nS
Turn-Off Fall Time	t_f		-	21	-	nS
Total Gate Charge	Q_g	$V_{DS}=75V, I_D=55A,$ $V_{GS}=10V$	-	150		nC
Gate-Source Charge	Q_{gs}		-	50		nC
Gate-Drain Charge	Q_{gd}		-	26		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_F=I_S$	-		1.2	V
Diode Forward Current (Note 2)	I_S		-	-	110	A
Reverse Recovery Time	t_{rr}	$T_J = 25^\circ\text{C}, I_F = I_S$ $di/dt = 100A/\mu\text{s}$ (Note 3)	-	140		nS
Reverse Recovery Charge	Q_{rr}		-	498		nC

Notes:

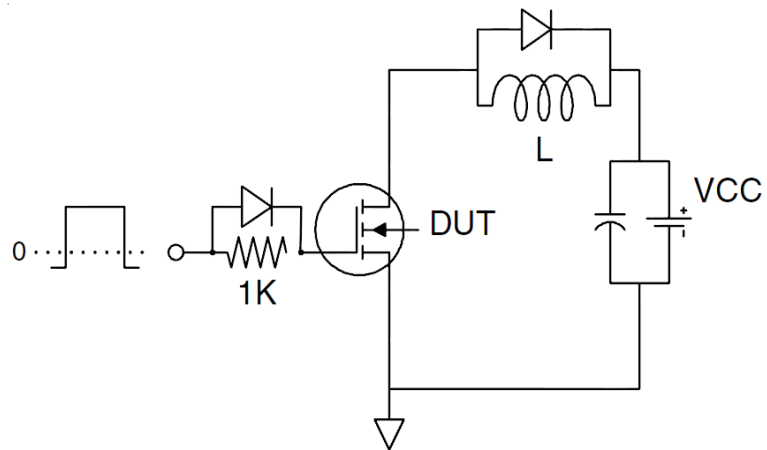
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition : $T_J=25^\circ\text{C}, V_{DD}=50V, V_G=10V, L=0.5\text{mH}, R_G=25\Omega$

Test Circuit

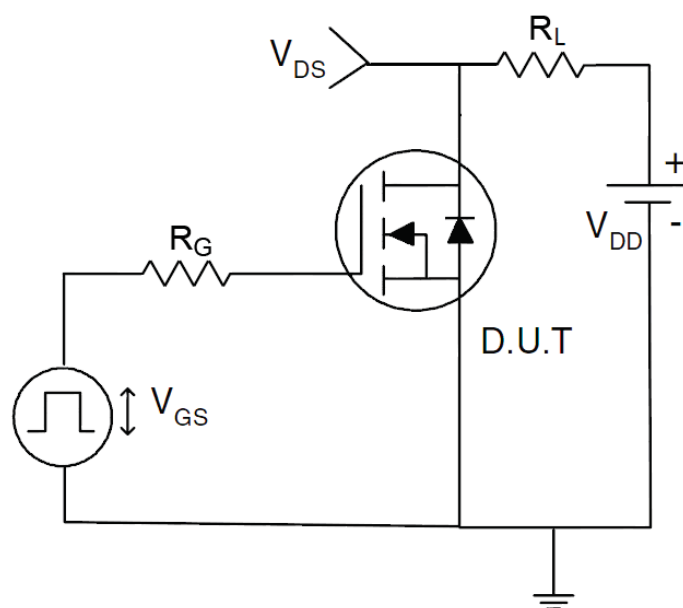
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



RATING AND CHARACTERISTICS CURVES (RM110N150HD)

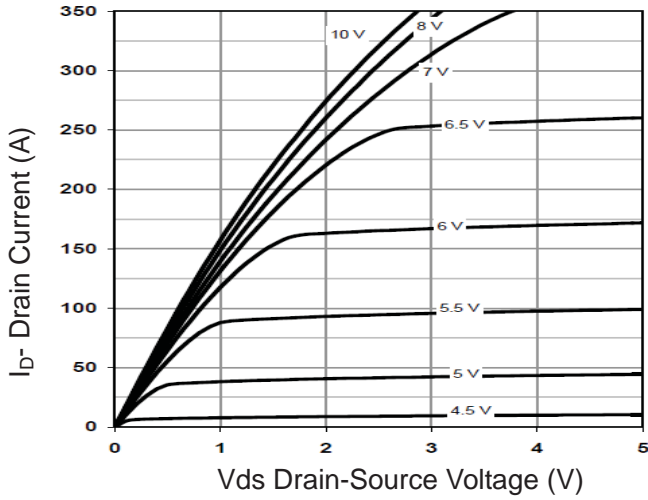


Figure 1 Output Characteristics

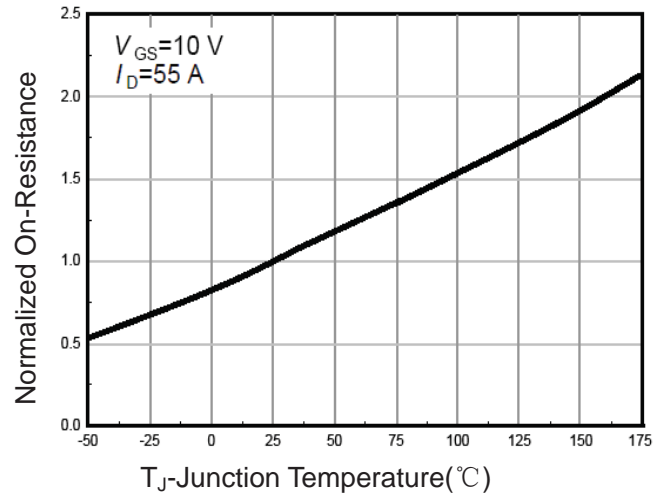


Figure 4 Rdson-Junction Temperature

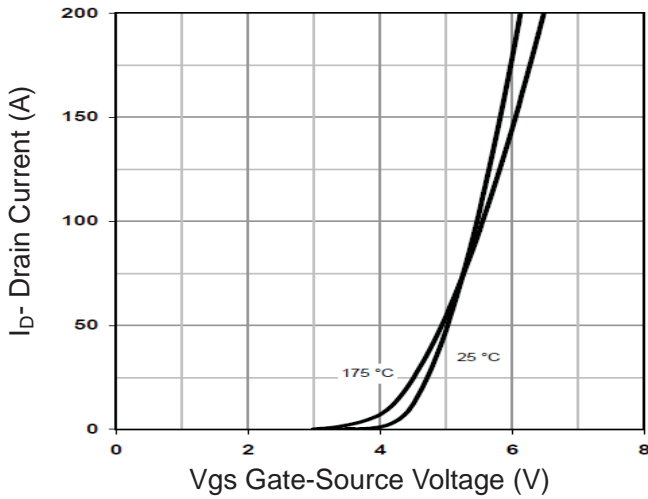


Figure 2 Transfer Characteristics

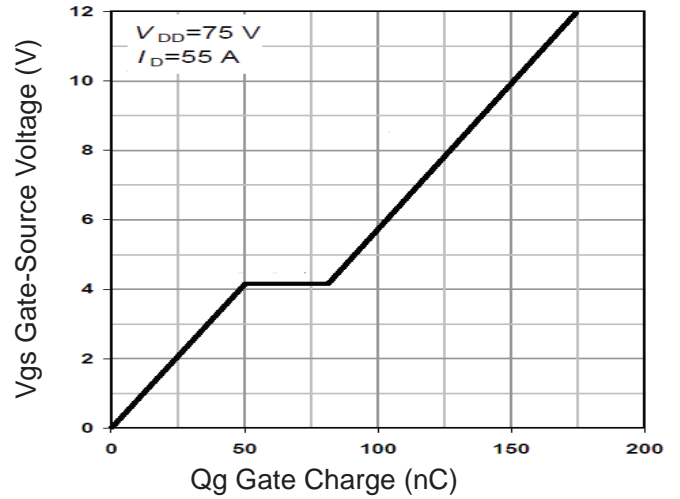


Figure 5 Gate Charge

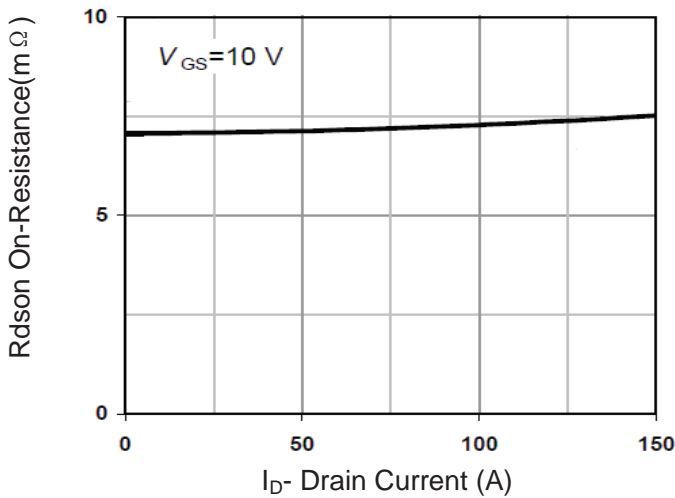


Figure 3 Rdson- Drain Current

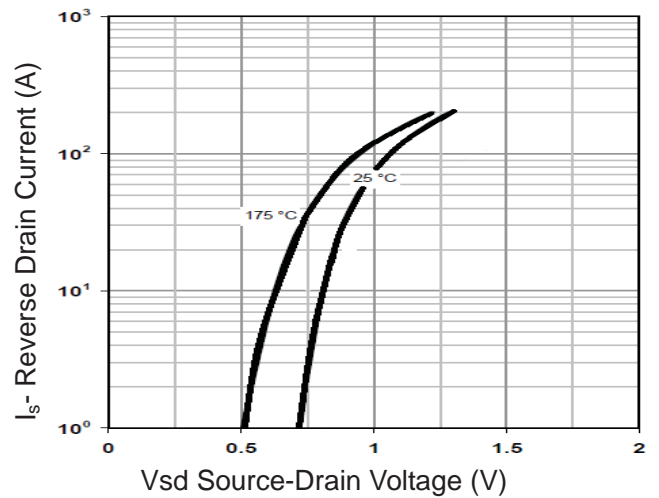


Figure 6 Source- Drain Diode Forward

RATING AND CHARACTERISTICS CURVES (RM110N150HD)

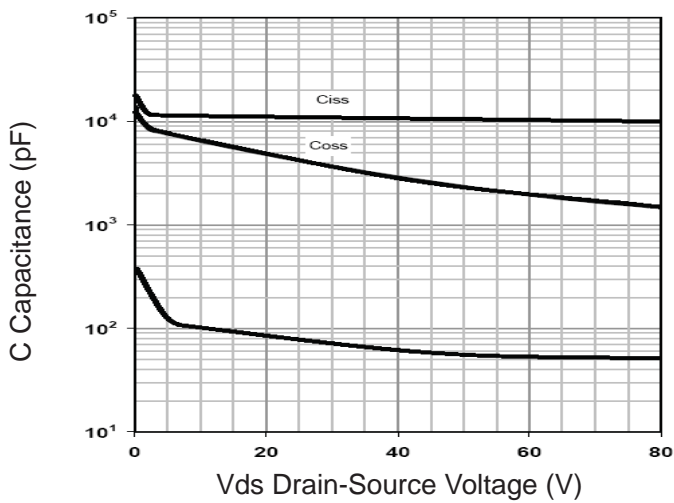


Figure 7 Capacitance vs Vds

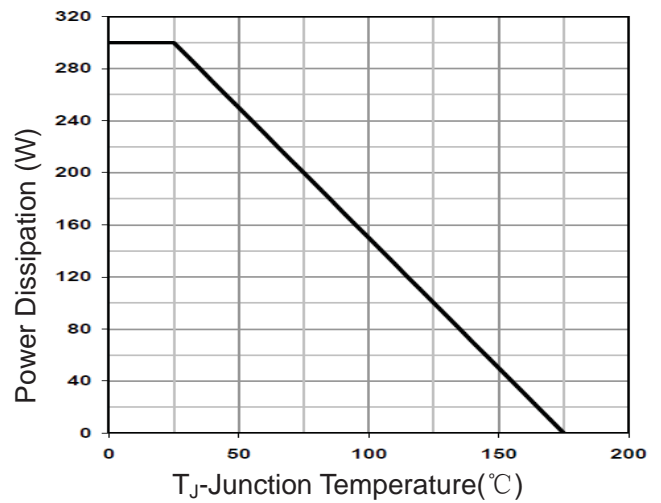


Figure 9 Power De-rating

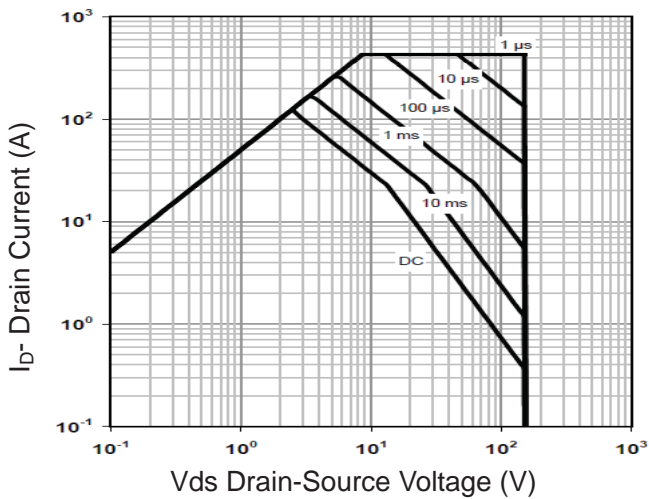


Figure 8 Safe Operation Area

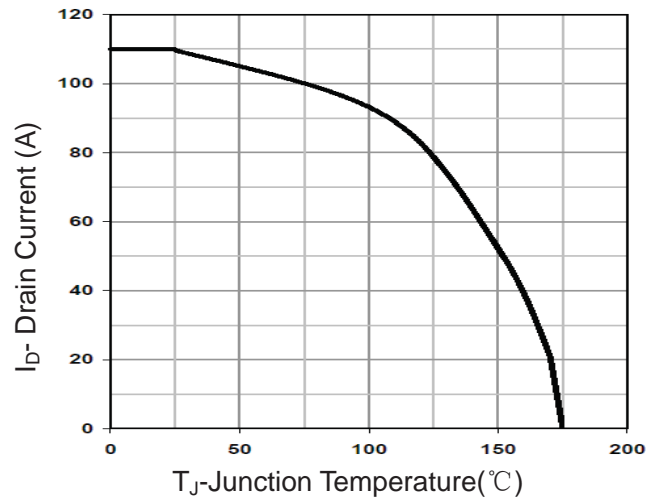


Figure 10 Current De-rating

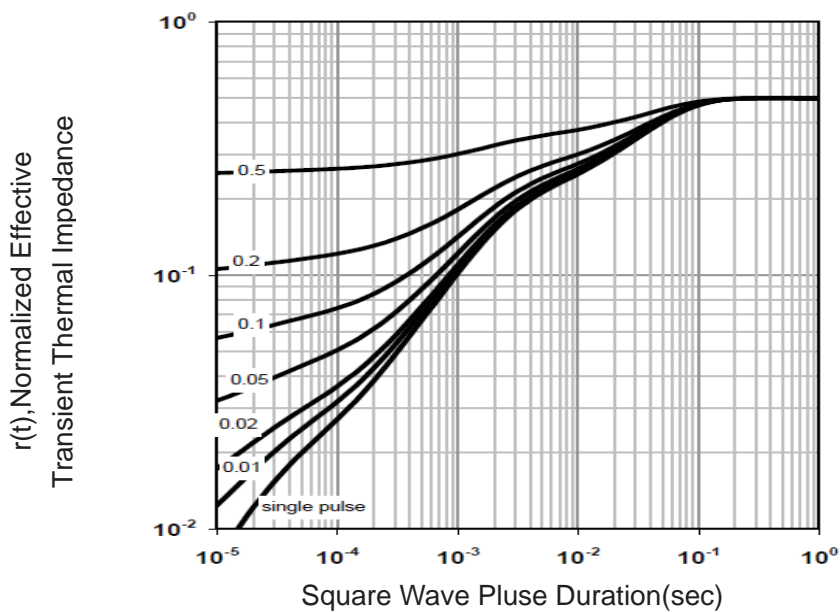
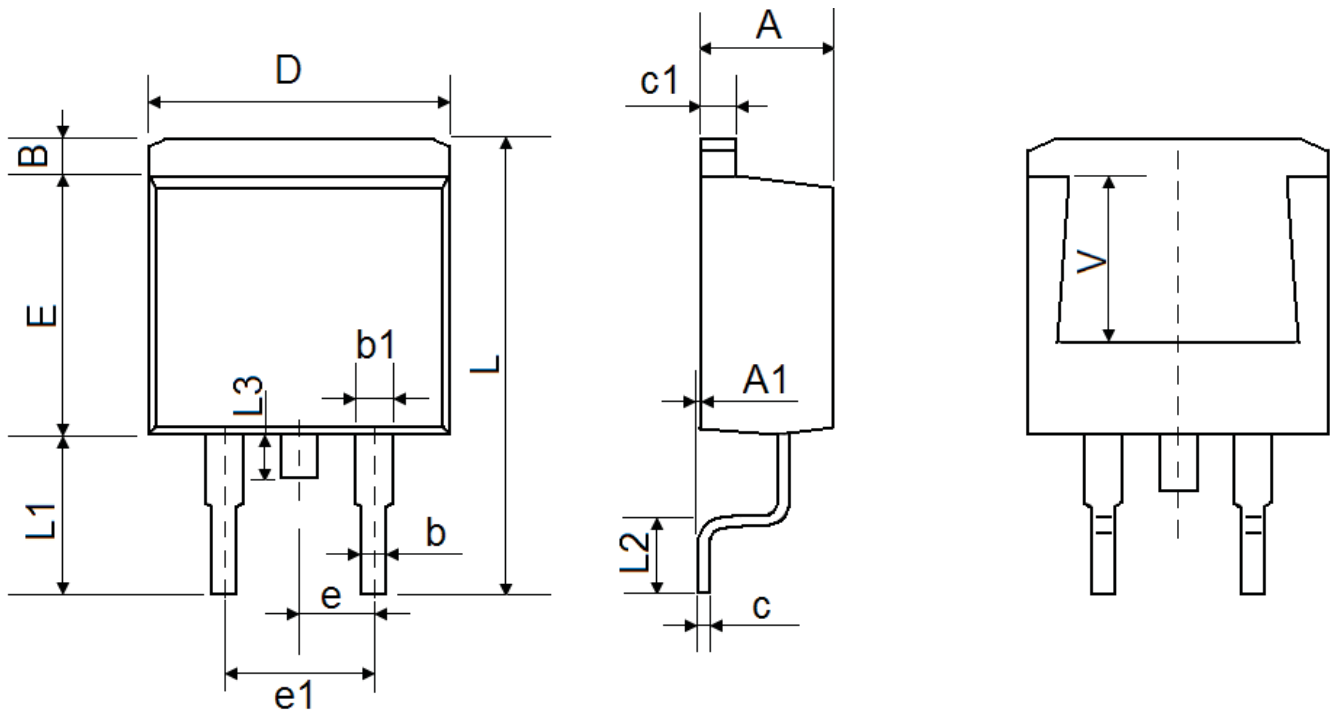


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-263-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.170	1.370	0.046	0.054
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
L	15.050	15.450	0.593	0.608
L1	5.080	5.480	0.200	0.216
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
V	5.600 REF		0.220 REF	

DISCLAIMER NOTICE

Rectron Inc reserves the right to make changes without notice to any product specification herein, to make corrections, modifications, enhancements or other changes. Rectron Inc or anyone on its behalf assumes no responsibility or liability for any errors or inaccuracies. Data sheet specifications and its information contained are intended to provide a product description only. "Typical" parameters which may be included on RECTRON data sheets and/ or specifications can and do vary in different applications and actual performance may vary over time. Rectron Inc does not assume any liability arising out of the application or use of any product or circuit.

Rectron products are not designed, intended or authorized for use in medical, life-saving implant or other applications intended for life-sustaining or other related applications where a failure or malfunction of component or circuitry may directly or indirectly cause injury or threaten a life without expressed written approval of Rectron Inc. Customers using or selling Rectron components for use in such applications do so at their own risk and shall agree to fully indemnify Rectron Inc and its subsidiaries harmless against all claims, damages and expenditures.